Electronic Supplementary Information

Direct imprint of MoS₂ flakes on the patterned gate for nanosheet transistors†

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Fig. S1 Optical microscopy images of (a) an exfoliated few layer-thin MoS$_2$ attached on PDMS, (b) precisely imprinted MoS$_2$ on patterned Au gate electrode, and (c) a bottom-gate MoS$_2$ FET with S/D pattern of Au/Ti. Note that we use an identical MoS$_2$ flake for all process steps.
Fig. S2 Optical microscopy images of Tr3 device on glass, which has non-gated region in its FET channel: (a) before and (b) after S/D contact.